**Vishay Semiconductors** 

# High Performance Schottky Rectifier, 240 A



www.vishay.com

PRODUCT SUMMARY				
I <sub>F(AV)</sub>	240 A			
V <sub>R</sub>	150 V			
Package	HALF-PAK (D-67)			
Circuit	Single diode			

### FEATURES

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- · Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### DESCRIPTION

The VS-249NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
I <sub>F(AV)</sub>	Rectangular waveform	240	А		
V <sub>RRM</sub>		150	V		
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	20 000	А		
V <sub>F</sub>	240 A <sub>pk</sub> , T <sub>J</sub> = 125 °C	0.78	V		
TJ	Range	-55 to +175	°C		

VOLTAGE RATINGS					
PARAMETER	SYMBOL	VS-249NQ150PbF	UNITS		
Maximum DC reverse voltage	V <sub>R</sub>	150	V		
Maximum working peak reverse voltage	V <sub>RWM</sub>	150	v		

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current See fig. 5	I <sub>F(AV)</sub>	50 % duty cycle at $T_{C}$ = 121 °C, rectangular waveform		240	
Maximum peak one cycle non-repetitive surge current	las	5 µs sine or 3 µs rect. pulse Following any rated load condition and with		20 000	А
See fig. 7	I <sub>FSM</sub>	10 ms sine or 6 ms rect. pulse	rated V <sub>RRM</sub> applied	2300	
Non-repetitive avalanche energy	E <sub>AS</sub>	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 5.5 A, L = 1 mH		15	mJ
Repetitive avalanche current	I <sub>AR</sub>	Current decaying linearly to zero in 1 $\mu$ s Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical		1	А

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
	V <sub>FM</sub> <sup>(1)</sup>	240 A	T <sub>J</sub> = 25 °C	1.21	V
Maximum forward voltage drop per leg		480 A		1.65	
See fig. 1		240 A	T <sub>.1</sub> = 125 °C	0.78	
		480 A	1j = 125 0	0.94	
Maximum reverse leakage current per leg See fig. 2	I <sub>RM</sub>	T <sub>J</sub> = 25 °C	$V_{B} = Rated V_{B}$	6	mA
		T <sub>J</sub> = 125 °C	VR - naleu VR	85	
Maximum junction capacitance	CT	$V_R$ = 5 $V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		6000	pF
Typical series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane		5.0	nH
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>		10 000	V/µs

Note

 $^{(1)}\,$  Pulse width < 300  $\mu s,$  duty cycle < 2  $\,\%$ 

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage tem	perature range	TJ, T <sub>Stg</sub>		-55 to 175	°C
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.19	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.05	
Approximate weight				30	g
				1.06	oz.
•• •• •	minimum			3 (26.5)	N · m (lbf · in)
Mounting torque	maximum		Non lubricated threads	4 (35.4)	
Terminal torque —	minimum		Non-lubricated threads	3.4 (30)	
	maximum			5 (44.2)	
Case style				HALF-PAK module	

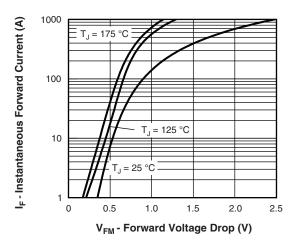
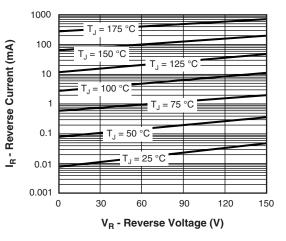
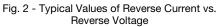


Fig. 1 - Maximum Forward Voltage Drop Characteristics





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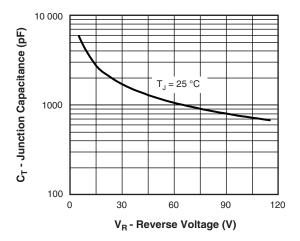


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

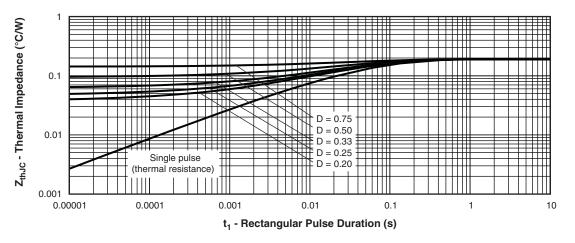
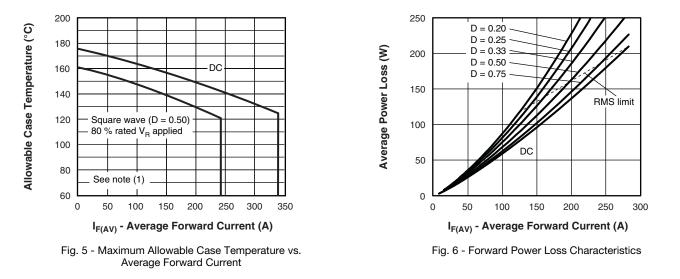


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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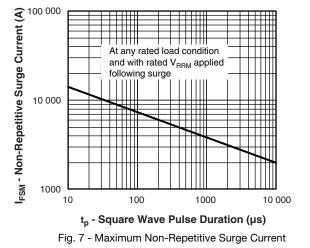
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## VS-249NQ150PbF

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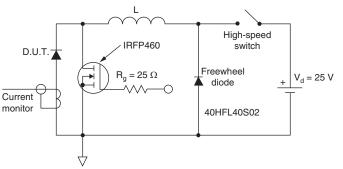
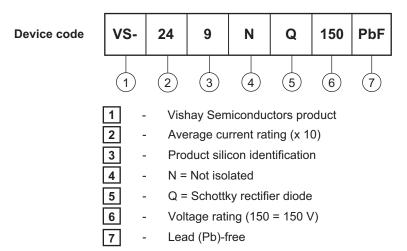


Fig. 8 - Unclamped Inductive Test Circuit

#### Note

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

### **ORDERING INFORMATION TABLE**



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<sup>&</sup>lt;sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

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17.5 (0.69) 16.5 (0.65)



### **DIMENSIONS** in millimeters (inches)

SHAY





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